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# Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









### **Dual High-Voltage Trench MOS Barrier Schottky Rectifier**

Ultra Low  $V_F = 0.420 \text{ V}$  at  $I_F = 5 \text{ A}$ 



#### **FEATURES**





Low forward voltage drop, low power losses



· High efficiency operation

RoHS

- Low thermal resistance
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

#### TYPICAL APPLICATIONS

For use in high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

| PRIMARY CHARACTERISTICS                 |          |  |  |  |
|---|----------|--|--|--|
| I <sub>F(AV)</sub>                      | 2 x 20 A |  |  |  |
| V <sub>RRM</sub>                        | 100 V    |  |  |  |
| I <sub>FSM</sub>                        | 250 A    |  |  |  |
| V <sub>F</sub> at I <sub>F</sub> = 20 A | 0.67 V   |  |  |  |
| T <sub>J</sub> max.                     | 150 °C   |  |  |  |

#### **MECHANICAL DATA**

Case: TO-247AD (TO-3P)

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class

1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs Maximum

| PARAMETER  Maximum repetitive peak reverse voltage   |   | SYMBOL                            | V40100PG      | UNIT |
|--|---|-----------------------------------|---------------|------|
|  |   | V <sub>RRM</sub>                  | 100           | V    |
| Maximum average forward rectified (Fig. 1)   | per device per diode I <sub>F(AV)</sub> 40 20 |                                   | А             |      |
| Peak forward surge current 10 ms single half sine-<br>superimposed on rated load per diode | I <sub>FSM</sub>                              | 250                               | А             |      |
| Peak repetitive reverse current per diode at $t_p$ = 2 $\mu$ s, 1 kHz                      |   | I <sub>RRM</sub>                  | 1.0           | Α    |
| Voltage rate of change (rated V <sub>R</sub> )   |   | dV/dt                             | 10 000        | V/µs |
| Operating junction and storage temperature range   |   | T <sub>J</sub> , T <sub>STG</sub> | - 40 to + 150 | °C   |



| <b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted) |  |   |                  |                         |                |          |  |
|---|--|---|------------------|-------------------------|----------------|----------|--|
| PARAMETER   | TEST CONDITIONS  |   | SYMBOL           | TYP.                    | MAX.           | UNIT     |  |
| Breakdown voltage   | I <sub>R</sub> = 1.0 mA  | T <sub>J</sub> = 25 °C                            | $V_{BR}$         | 100                     | -              | V        |  |
| Instantaneous forward voltage per diode <sup>(1)</sup>                            | $I_F = 5 A$ $I_F = 10 A$ $I_F = 20 A$                                  | T <sub>J</sub> = 25 °C                            | V <sub>F</sub>   | 0.490<br>0.572<br>0.731 | -<br>-<br>0.81 | V        |  |
|   | I <sub>F</sub> = 5 A<br>I <sub>F</sub> = 10 A<br>I <sub>F</sub> = 20 A | T <sub>J</sub> = 125 °C                           |                  | 0.42<br>0.50<br>0.67    | -<br>-<br>0.73 |          |  |
| Reverse current at rated V <sub>R</sub> per diode <sup>(2)</sup>                  | V <sub>R</sub> = 70 V  | T <sub>J</sub> = 25 °C<br>T <sub>J</sub> = 125 °C | . I <sub>R</sub> | 8.4<br>7.4              | 300<br>15      | μA<br>mA |  |
|   | V <sub>R</sub> = 100 V   | T <sub>J</sub> = 25 °C<br>T <sub>J</sub> = 125 °C |                  | 40.5<br>18.2            | 500<br>35      | μA<br>mA |  |

#### Notes

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

| THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted) |                |          |      |  |
|---|----------------|----------|------|--|
| PARAMETER   | SYMBOL         | V40100PG | UNIT |  |
| Typical thermal resistance per diode                                    | $R_{	heta JC}$ | 2.0      | °C/W |  |

| ORDERING INFORMATION |                 |                        |               |               |  |  |  |
|----------------------|-----------------|------------------------|---------------|---------------|--|--|--|
| PREFERRED P/N        | UNIT WEIGHT (g) | PREFERRED PACKAGE CODE | BASE QUANTITY | DELIVERY MODE |  |  |  |
| V40100PG-E3/45       | 6.109           | 45                     | 30/Tube       | Tube          |  |  |  |

#### **RATINGS AND CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25 °C unless otherwise noted)

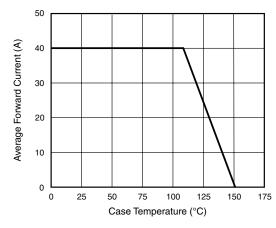


Figure 1. Forward Current Derating Curve

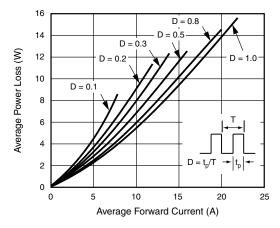


Figure 2. Forward Power Loss Characteristics Per Diode



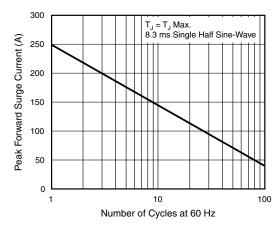


Figure 3. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

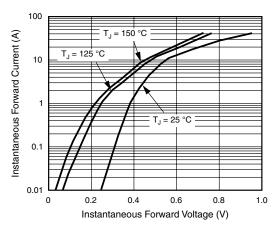


Figure 4. Typical Instantaneous Forward Characteristics Per Diode

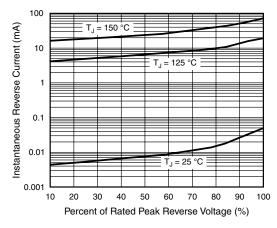


Figure 5. Typical Reverse Characteristics Per Diode

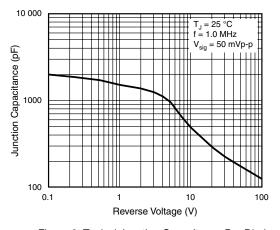


Figure 6. Typical Junction Capacitance Per Diode

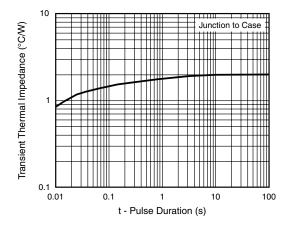
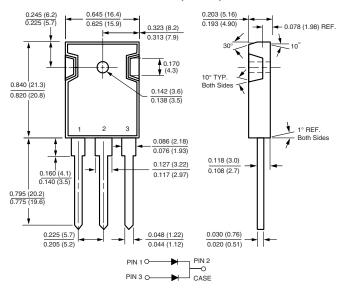


Figure 7. Typical Transient Thermal Impedance Per Diode



### **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)

### TO-247AD (TO-3P)





Vishay

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